

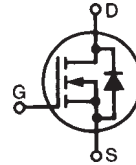
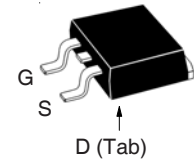
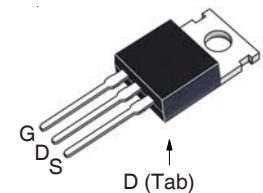


**Trench™  
Power MOSFET**
**IXTA160N10T  
IXTP160N10T**

$$V_{DSS} = 100V$$

$$I_{D25} = 160A$$

$$R_{DS(on)} \leq 7.0m\Omega$$

 N-Channel Enhancement Mode  
Avalanche Rated

**TO-263  
(IXTA)**

**TO-220  
(IXTP)**

 G = Gate      D = Drain  
S = Source    Tab = Drain

| Symbol        | Test Conditions  | Maximum Ratings    |            |
|---------------|--|--------------------|------------|
| $V_{DSS}$     | $T_J = 25^\circ C$ to $175^\circ C$                                | 100                | V          |
| $V_{DGR}$     | $T_J = 25^\circ C$ to $175^\circ C$ , $R_{GS} = 1M\Omega$          | 100                | V          |
| $V_{GSS}$     | Continuous   | $\pm 20$           | V          |
| $V_{GSM}$     | Transient  | $\pm 30$           | V          |
| $I_{D25}$     | $T_C = 25^\circ C$ (Chip Capability)                               | 160                | A          |
| $I_{L(RMS)}$  | Lead Current Limit, RMS  | 120                | A          |
| $I_{DM}$      | $T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$               | 430                | A          |
| $I_A$         | $T_C = 25^\circ C$   | 25                 | A          |
| $E_{AS}$      | $T_C = 25^\circ C$   | 500                | mJ         |
| $dV/dt$       | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 175^\circ C$ | 3                  | V/ns       |
| $P_D$         | $T_C = 25^\circ C$   | 430                | W          |
| $T_J$         |  | -55 ... +175       | $^\circ C$ |
| $T_{JM}$      |  | 175                | $^\circ C$ |
| $T_{stg}$     |  | -55 ... +175       | $^\circ C$ |
| $T_L$         | Maximum Lead Temperature for Soldering                             | 300                | $^\circ C$ |
| $T_{SOLD}$    | 1.6 mm (0.062in.) from Case for 10s                                | 260                | $^\circ C$ |
| $F_C$         | Mounting Force (TO-263)  | 10..65 / 2.2..14.6 | N/lb       |
| $M_d$         | Mounting Torque (TO-220)   | 1.13 / 10          | Nm/lb.in   |
| <b>Weight</b> | TO-263   | 2.5                | g          |
|               | TO-220   | 3.0                | g          |

**Features**

- Ultra-Low On Resistance
- Avalanche Rated
- Low Package Inductance
  - Easy to Drive and to Protect
- $175^\circ C$  Operating Temperature
- Fast Intrinsic Diode

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- Automotive
  - Motor Drives
  - 42V Power Bus
  - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary Switch for 24V and 48V Systems
- Distributed Power Architectures and VRMs
- Electronic Valve Train Systems
- High Current Switching Applications
- High Voltage Synchronous Rectifier

| Symbol       | Test Conditions<br>( $T_J = 25^\circ C$ Unless Otherwise Specified) | Characteristic Values |      |              |
|--------------|---|-----------------------|------|--------------|
|              |   | Min.                  | Typ. | Max.         |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 250\mu A$                                    | 100                   |      | V            |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\mu A$                                | 2.5                   |      | 4.5 V        |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                                  |                       |      | $\pm 200$ nA |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$                                  |                       |      | 5 $\mu A$    |
|              | $T_J = 150^\circ C$   |                       |      | 250 $\mu A$  |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 25A$ , Notes 1 & 2                          | 6.1                   | 7.0  | m $\Omega$   |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)   | Characteristic Values |      |                        |
|--------------|---|-----------------------|------|------------------------|
|              |   | Min.                  | Typ. | Max.                   |
| $g_{fs}$     | $V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1   | 65                    | 102  | S                      |
| $C_{iss}$    | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$  |                       | 6600 | pF                     |
| $C_{oss}$    |   |                       | 880  | pF                     |
| $C_{rss}$    |   |                       | 135  | pF                     |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 25\text{A}$<br>$R_G = 5\Omega$ (External) |                       | 33   | ns                     |
| $t_r$        |   |                       | 61   | ns                     |
| $t_{d(off)}$ |   |                       | 49   | ns                     |
| $t_f$        |   |                       | 42   | ns                     |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 25\text{A}$   |                       | 132  | nC                     |
| $Q_{gs}$     |   |                       | 37   | nC                     |
| $Q_{gd}$     |   |                       | 40   | nC                     |
| $R_{thJC}$   |   |                       |      | $0.35^\circ\text{C/W}$ |
| $R_{thCH}$   | TO-220  | 0.50                  |      | $^\circ\text{C/W}$     |

### Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)                          | Characteristic Values |      |       |
|----------|--|-----------------------|------|-------|
|          |  | Min.                  | Typ. | Max.  |
| $I_S$    | $V_{GS} = 0\text{V}$   |                       |      | 160 A |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$  |                       |      | 430 A |
| $V_{SD}$ | $I_F = 25\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1   |                       |      | 1.0 V |
| $t_{rr}$ | $I_F = 25\text{A}$ , $V_{GS} = 0\text{V}$<br>$-di/dt = 100\text{A}/\mu\text{s}$ , $V_R = 50\text{V}$ |                       | 60   | ns    |

- Notes: 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .  
2. On through-hole packages,  $R_{DS(on)}$  Kelvin test contact location must be 5mm or less from the package body.

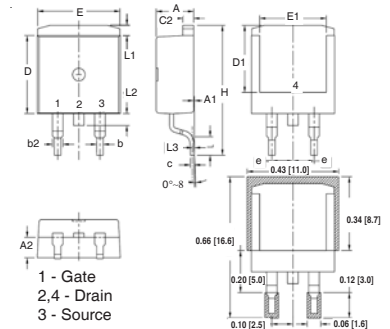
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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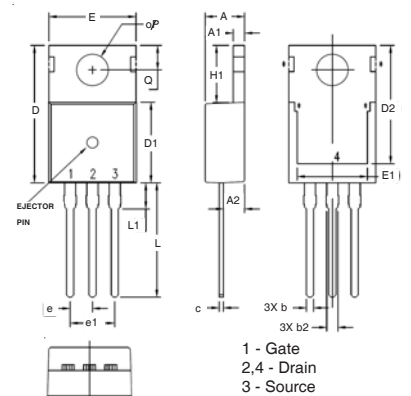
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592; 4,931,844; 5,049,961; 5,237,481; 6,162,665; 6,404,065 B1; 6,683,344; 6,727,585; 7,005,734 B2; 7,157,338B2; 4,860,072; 5,017,508; 5,063,307; 5,381,025; 6,259,123 B1; 6,534,343; 6,710,405 B2; 6,759,692; 7,063,975 B2; 4,881,106; 5,034,796; 5,187,117; 5,486,715; 6,306,728 B1; 6,583,505; 6,710,463; 6,771,478 B2; 7,071,537

### TO-263 Outline



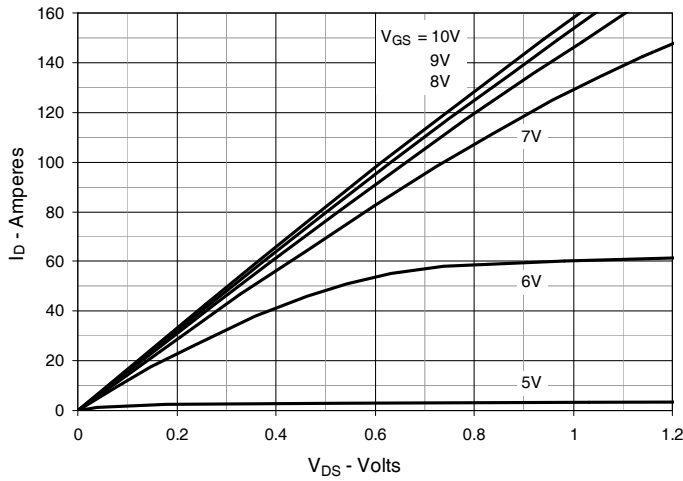
| SYM | INCHES   |      | MILLIMETER |       |
|-----|----------|------|------------|-------|
|     | MIN      | MAX  | MIN        | MAX   |
| A   | .170     | .185 | 4.30       | 4.70  |
| A1  | .000     | .008 | 0.00       | 0.20  |
| A2  | .091     | .098 | 2.30       | 2.50  |
| b   | .028     | .035 | 0.70       | 0.90  |
| b2  | .046     | .060 | 1.18       | 1.52  |
| C   | .018     | .024 | 0.45       | 0.60  |
| C2  | .049     | .060 | 1.25       | 1.52  |
| D   | .340     | .370 | 8.63       | 9.40  |
| D1  | .300     | .327 | 7.62       | 8.30  |
| E   | .380     | .410 | 9.65       | 10.41 |
| E1  | .270     | .330 | 6.86       | 8.38  |
| e   | .100 BSC |      | 2.54 BSC   |       |
| H   | .580     | .620 | 14.73      | 15.75 |
| L   | .075     | .105 | 1.91       | 2.67  |
| L1  | .039     | .060 | 1.00       | 1.52  |
| L2  | —        | .070 | —          | 1.77  |
| L3  | .010 BSC |      | 0.254 BSC  |       |

### TO-220 Outline

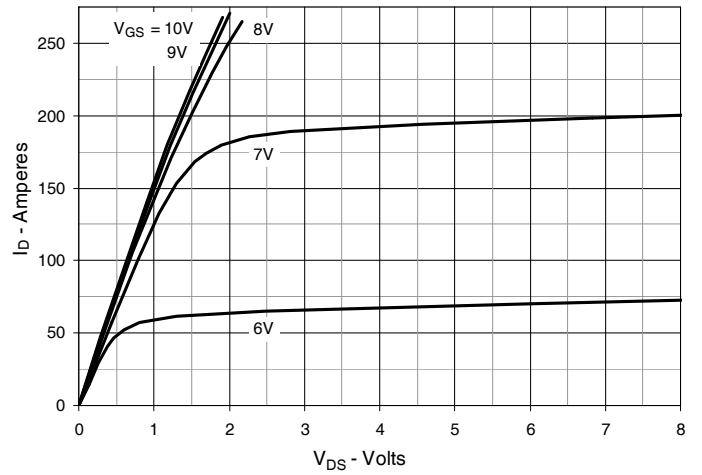


| SYM  | INCHES   |      | MILLIMETERS |       |
|------|----------|------|-------------|-------|
|      | MIN      | MAX  | MIN         | MAX   |
| A    | .169     | .185 | 4.30        | 4.70  |
| A1   | .047     | .055 | 1.20        | 1.40  |
| A2   | .079     | .106 | 2.00        | 2.70  |
| b    | .024     | .039 | 0.60        | 1.00  |
| b2   | .045     | .057 | 1.15        | 1.45  |
| c    | .014     | .026 | 0.35        | 0.65  |
| D    | .587     | .626 | 14.90       | 15.90 |
| D1   | .335     | .370 | 8.50        | 9.40  |
| (D2) | .500     | .531 | 12.70       | 13.50 |
| E    | .382     | .406 | 9.70        | 10.30 |
| (E1) | .283     | .323 | 7.20        | 8.20  |
| e    | .100 BSC |      | 2.54 BSC    |       |
| e1   | .200 BSC |      | 5.08 BSC    |       |
| H1   | .244     | .268 | 6.20        | 6.80  |
| L    | .492     | .547 | 12.50       | 13.90 |
| L1   | .110     | .154 | 2.80        | 3.90  |
| ∅P   | .134     | .150 | 3.40        | 3.80  |
| Q    | .106     | .126 | 2.70        | 3.20  |

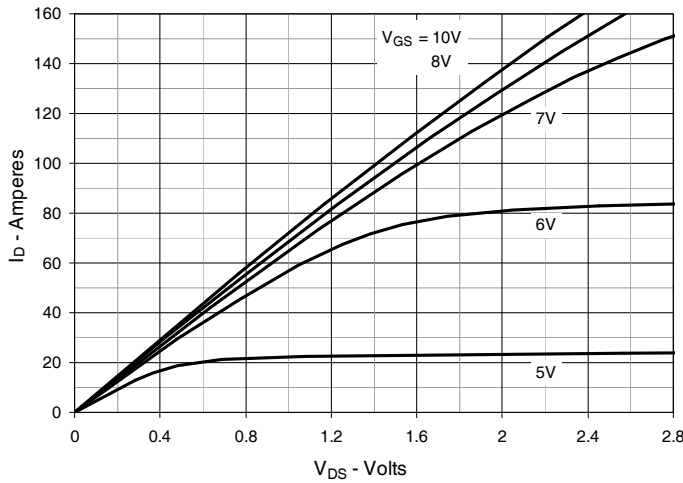
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



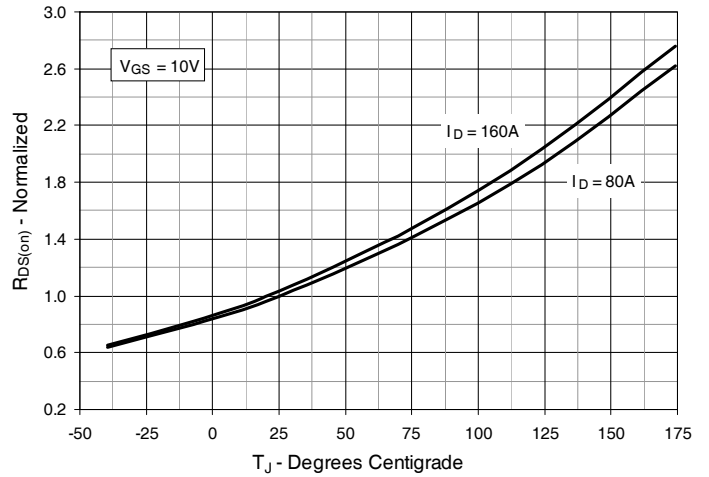
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



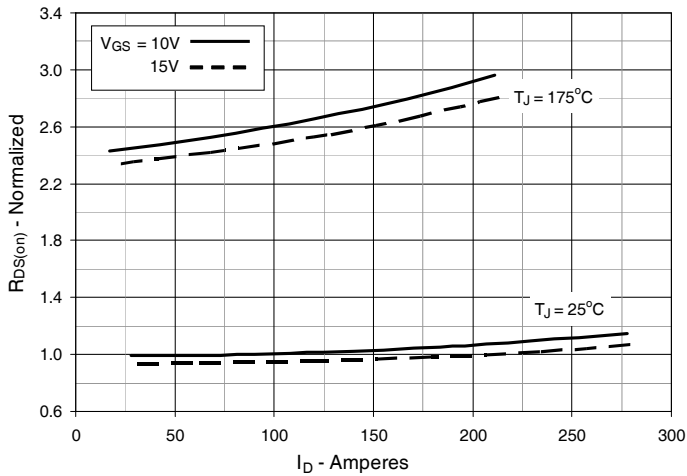
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



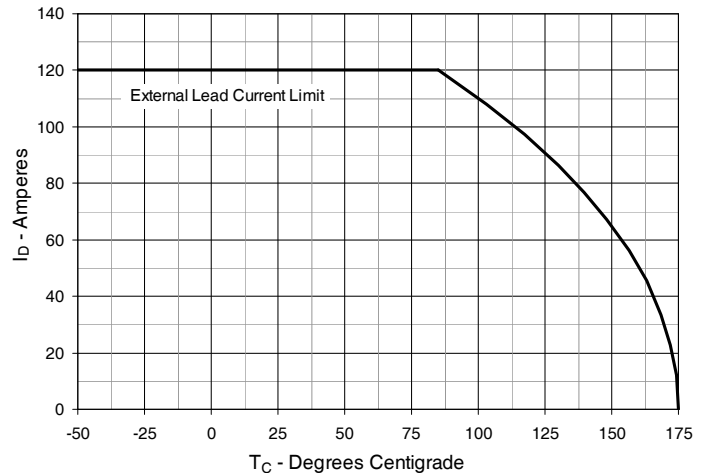
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 160\text{A}$  Value vs. Junction Temperature**



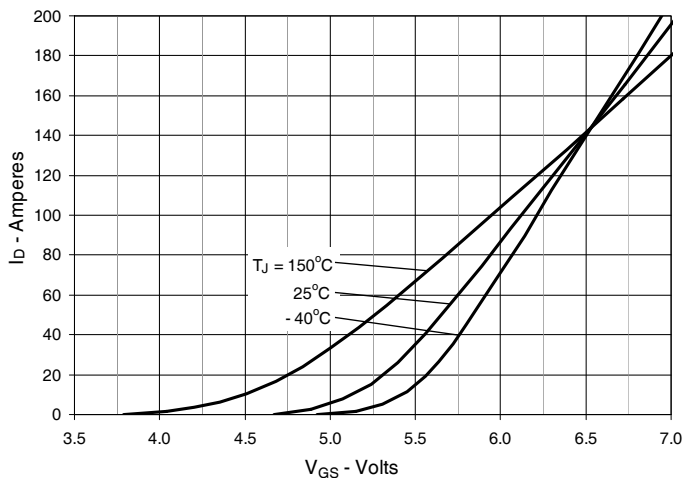
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 80\text{A}$  Value vs. Drain Current**



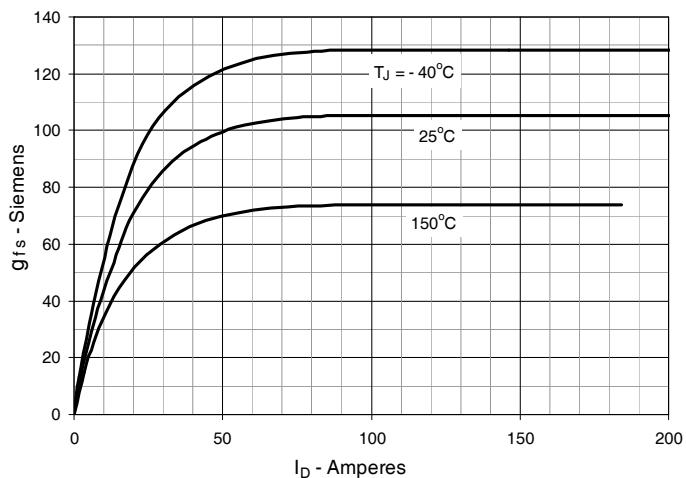
**Fig. 6. Drain Current vs. Case Temperature**



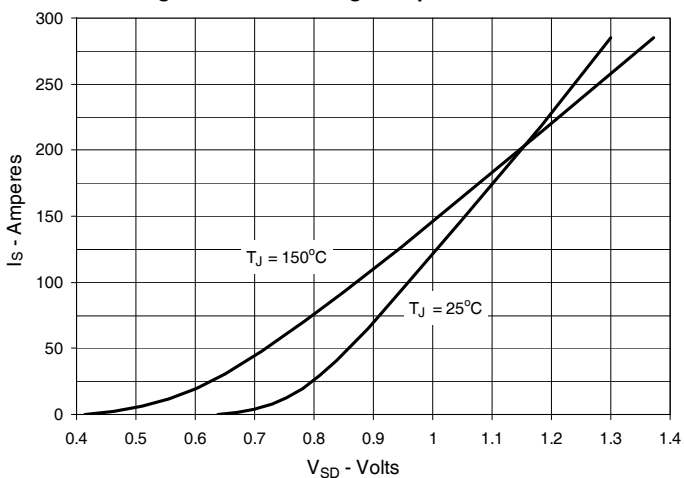
**Fig. 7. Input Admittance**



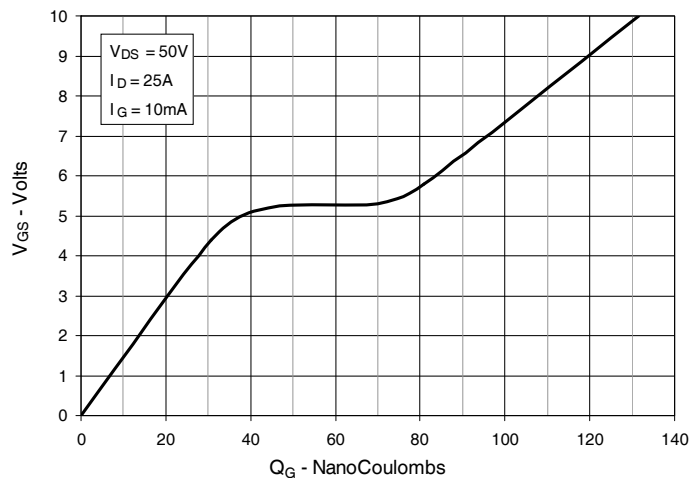
**Fig. 8. Transconductance**



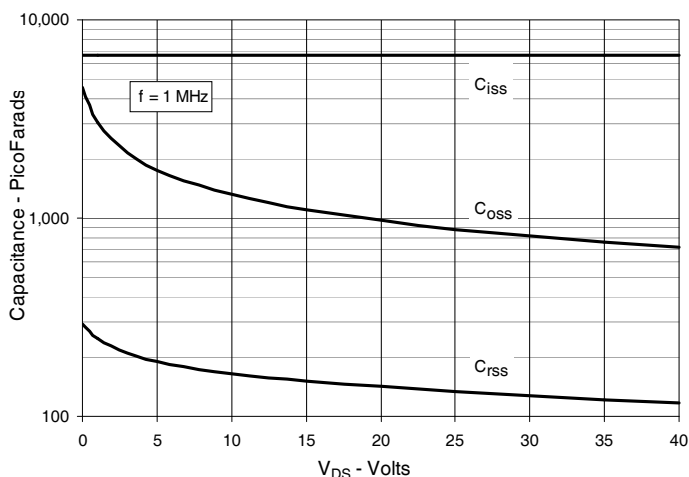
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



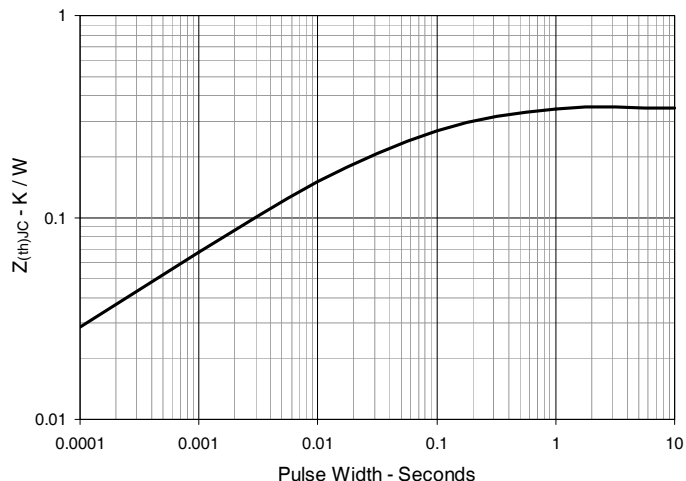
**Fig. 10. Gate Charge**



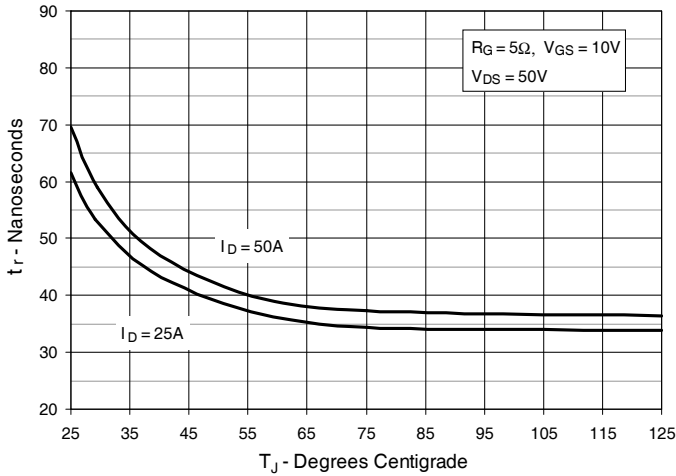
**Fig. 11. Capacitance**



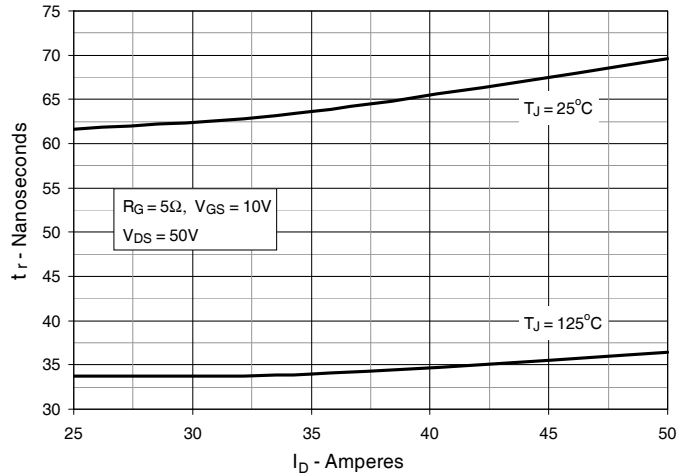
**Fig. 12. Maximum Transient Thermal Impedance**



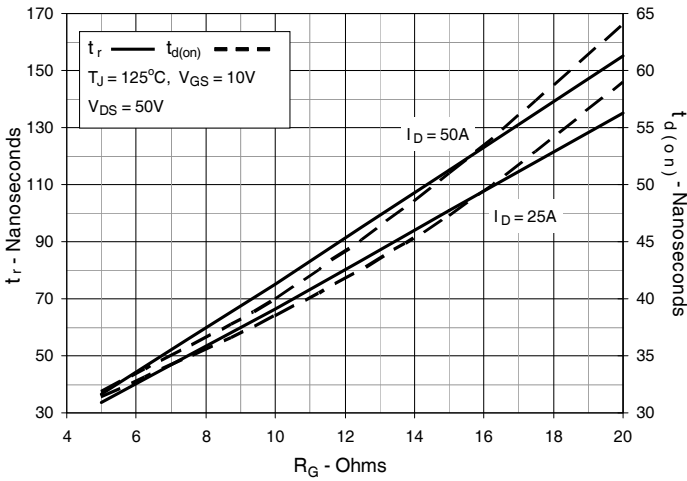
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



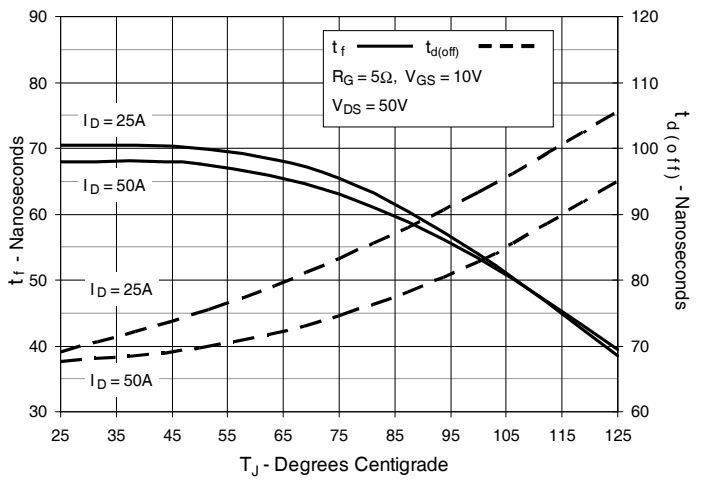
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



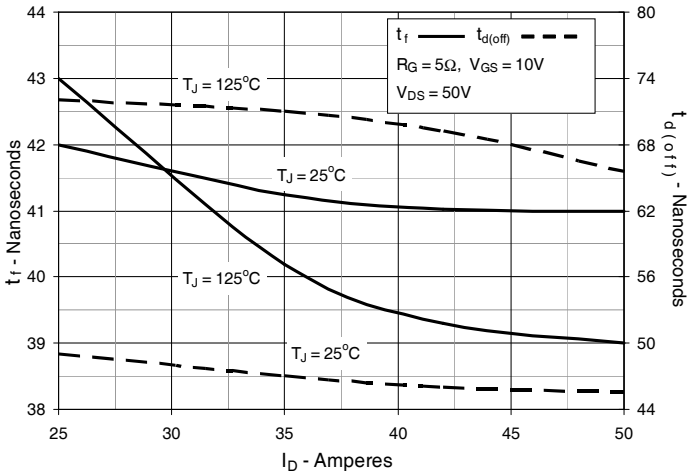
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



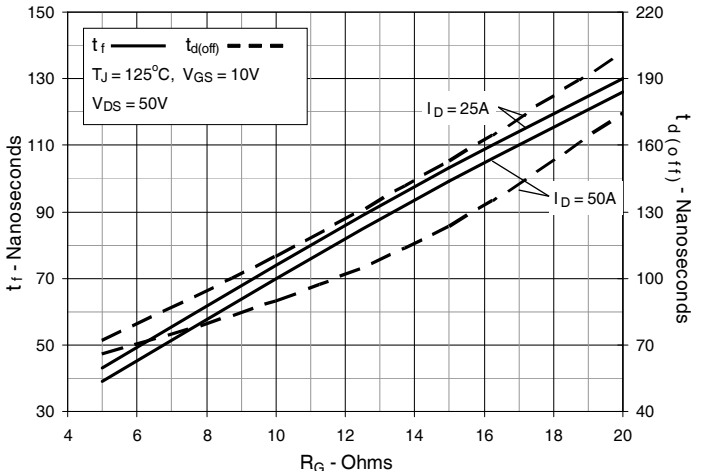
**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**





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